

**PD322PI** 2-division Chip Type Photodiode

T-41-53

## ■ Features

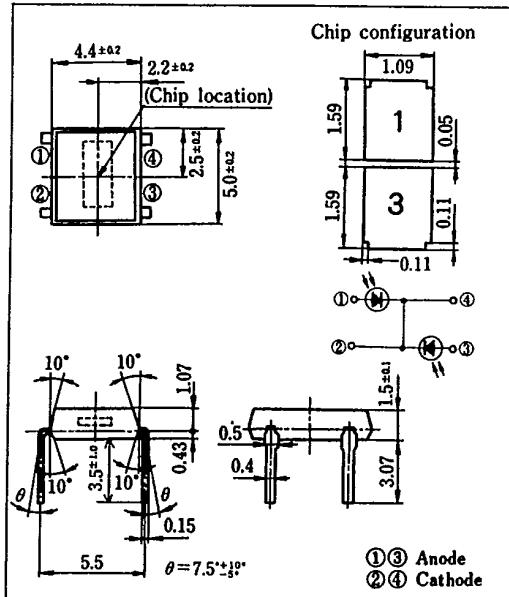
1. 2-division chip type
  2. Peak sensitivity wavelength  $\lambda_p$  : 980nm
  3. Transparent transfer mold package

## ■ Applications

1. VCR cameras
  2. Cameras

## ■ Outline Dimensions

(Unit : mm)



## ■ Absolute Maximum Ratings

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Reverse voltage	V <sub>R</sub>	30	V
Power dissipation	P	100	mW
Oprating temperature	T <sub>opr</sub>	-25~+80	°C
Storage temperature	T <sub>stg</sub>	-40~+80	°C
*1Soldering temperature	T <sub>sot</sub>	260	°C

\*3 For 3 seconds at the position of 1mm from the bottom face of resin package

## ■ Electro-optical Characteristics

(Ta=25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
* <sup>2</sup> Short circuit current	I <sub>sc</sub>	* <sup>3</sup> E <sub>V</sub> =100 Ήx	1.2	1.7	2.2	μA
Dark current	I <sub>d</sub>	V <sub>R</sub> =10V	—	—	20	nA
Terminal capacitance	C <sub>t</sub>	V <sub>R</sub> =10V, f=1MHz	—	5	15	pF
Peak sensitivity wavelength	λ <sub>p</sub>		930	980	1,010	nm
Response time	t <sub>r</sub> , t <sub>f</sub>	V <sub>R</sub> =10V, R <sub>L</sub> =1kΩ	—	70	—	ns

\*2 Values for 1 element. Measured with short-circuit between the anode and the cathode of non-measurement elements.

\*3  $E_v$  : Illuminance by CIE standard light source A (tungsten lamp)

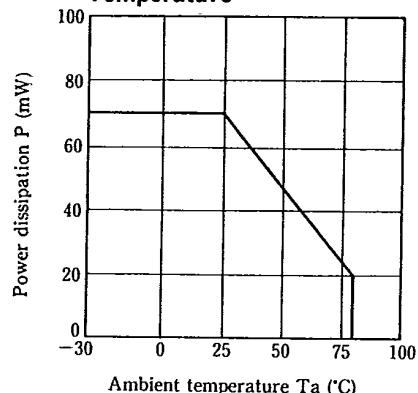
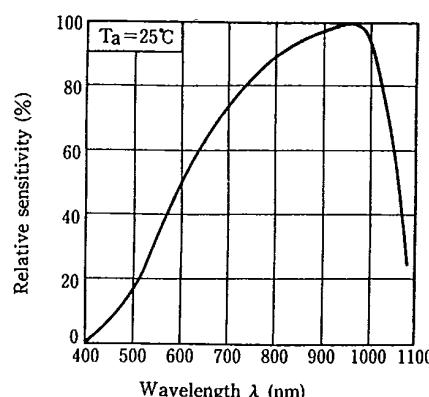
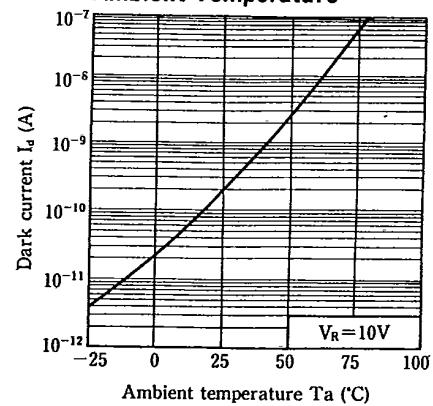
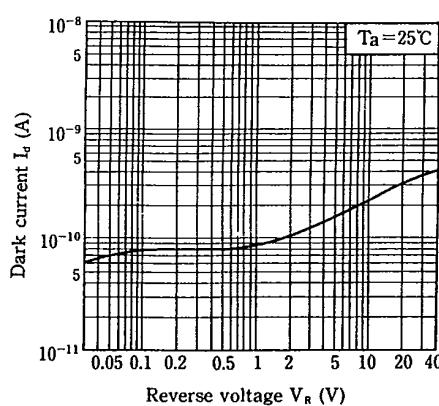
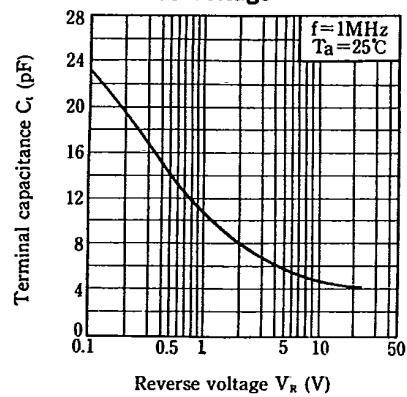
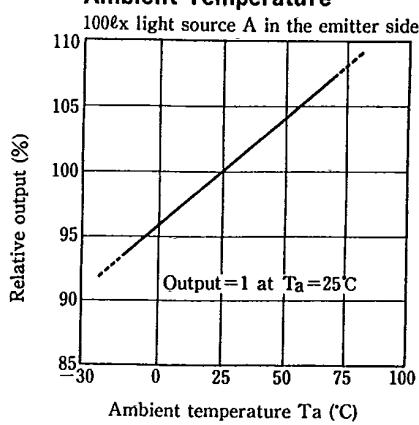
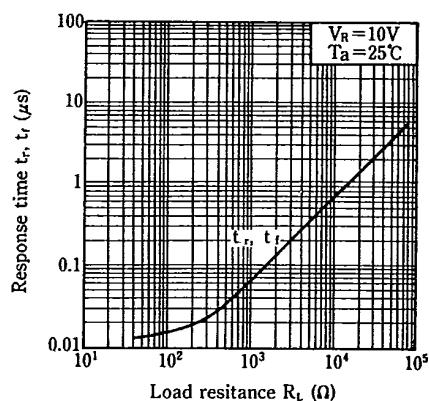
**Fig. 1 Power Dissipation vs. Ambient Temperature****Fig. 2 Spectral Sensitivity T-41-53****Fig. 3 Dark Current vs. Ambient Temperature****Fig. 4 Dark Current vs. Reverse Voltage****4****Fig. 5 Terminal Capacitance vs. Reverse Voltage****Fig. 6 Relative Output vs. Ambient Temperature**

Fig. 7 Response Time vs. Load Resistance



Test Circuit for Response Time

T-41-53

